

30kV 10mA HIGH VOLTAGE DIODES

G30FP is high reliability resin molded type high voltage diode in small size package which is sealed a multilayered mesa type silicon chip by epoxy resin.

Features

- High speed switching
- High Current
- High surge resistivity for CRT discharge
- High reliability design
- High Voltage

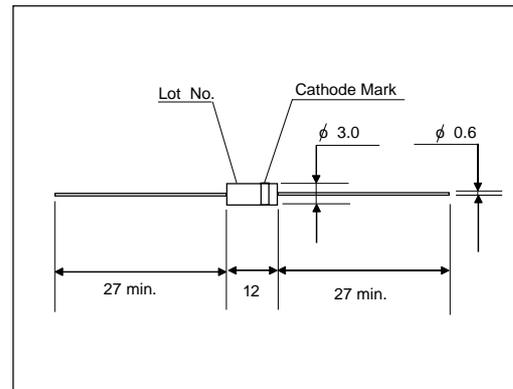
Applications

- X light Power supply
- Laser
- Voltage doubler circuit
- Microwave emission power

Maximum Ratings and Characteristics

- Absolute Maximum Ratings

Outline Drawings : mm



Cathode Mark

Type	Mark
G30FP	

Items	Symbols	Condition	G30FP	Units
Repetitive Peak Reverse Voltage	V_{RRM}		30	kV
Average Output Current	I_o	Ta=25°C, Resistive Load	10	mA
Surge Current	I_{FSM}		3.0	A _{peak}
Junction Temperature	T_j		150	°C
Allowable Operation Case Temperature	T_c		125	°C
Storage Temperature	T_{stg}		-40 to +150	°C

Electrical Characteristics (Ta=25°C Unless otherwise specified)

Items	Symbols	Conditions	G30FP	Units
Maximum Forward Voltage Drop	V_F	at 25°C, $I_F = I_{F(AV)}$	55	V
Maximum Reverse Current	IR1	at 25°C, $V_R = V_{RRM}$	0.2	uA
	IR2	at 100°C, $V_R = V_{RRM}$	5.0	uA
Maximum Reverse Recovery Time	T_{rr}	at 25°C	100	nS
Junction Capacitance	C_j	at 25°C, $V_R = 0V, f = 1MHz$	--	pF